



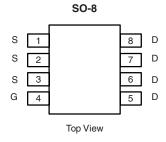
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 30	$0.042 \text{ at V}_{GS} = -10 \text{ V}$	- 5.7		
	0.055 at V _{GS} = - 6 V	- 5.0		
	0.070 at V _{GS} = - 4.5 V	- 4.4		

FEATURES

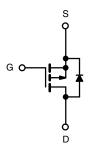
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si9435BDY-T1-E3 (Lead (Pb)-free)

Si9435BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	Γ _A = 25 °C, unles	ss otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 20		V	
Continuous Dusin Comment /T 450 90\8	T _A = 25 °C	- I _D	- 5.7	- 4.1	^	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.6	- 3.2		
Pulsed Drain Current		I _{DM}	- 30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.3	- 1.1		
	T _A = 25 °C	- P _D	2.5	1.3	W	
Maximum Power Dissipation ^a	T _A = 70 °C		1.6	0.8		
Operating Junction and Storage Temperature Rang	je	T _J , T _{stg}	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	40	50	°C/W
	Steady State		70	95	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	24	30	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

Si9435BDY

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.		Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1		
	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 70 °C			- 5	μΑ	
On-State Drain Current ^b	1-7	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			A	
	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 5				
		$V_{GS} = -10 \text{ V}, I_D = -5.7 \text{ A}$		0.033	0.042	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = -6 \text{ V}, I_D = -5 \text{ A}$		0.043	0.055		
		V _{GS} = - 4.5 V, I _D = - 4.4 A		0.056	0.070		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -5.7 \text{ A}$		13		S	
Diode Forward Voltage ^b	V_{SD}	$I_S = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.1	V	
Dynamic ^a							
Total Gate Charge	Q_g			16	24		
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.5 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			4.5		1	
Gate Resistance	R_g			8.8		Ω	
Turn-On Delay Time	t _{d(on)}			14	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	25		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=$ 6 Ω		42	70	ns	
Fall Time	t _f			30	50		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.2 A, dI/dt = 100 A/μs		30	60		

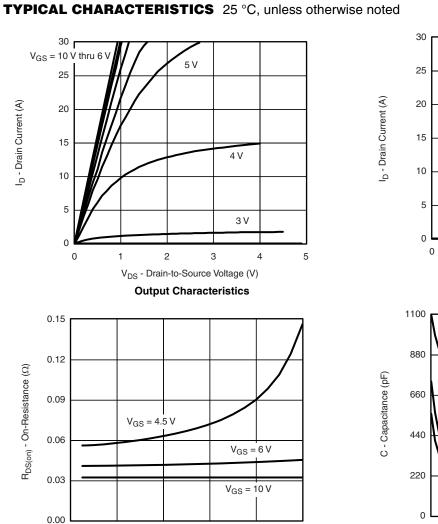
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$





I_D - Drain Current (A)

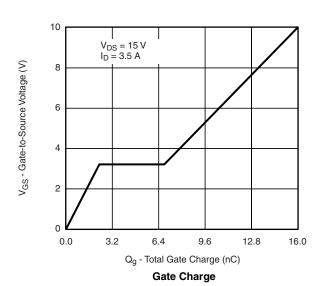
On-Resistance vs. Drain Current

12

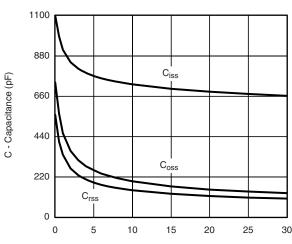
16

20

8

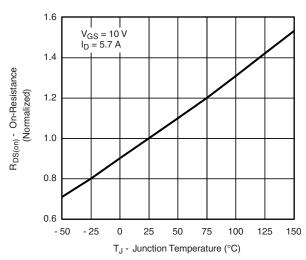


Transfer Characteristics



 $V_{\mbox{\footnotesize DS}}$ - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

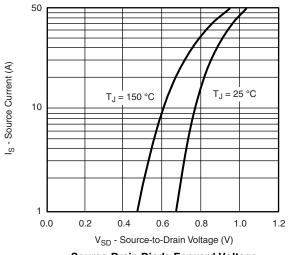
0

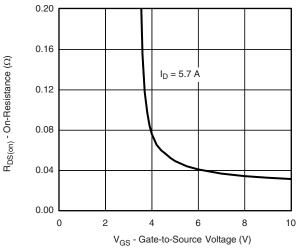
4

Vishay Siliconix

VISHAY

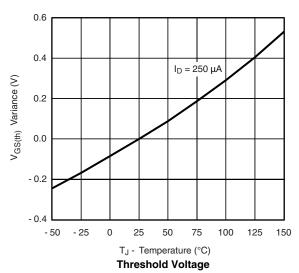
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

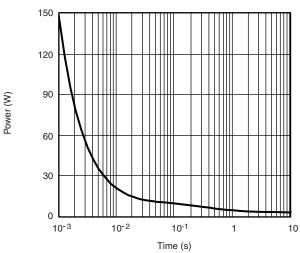




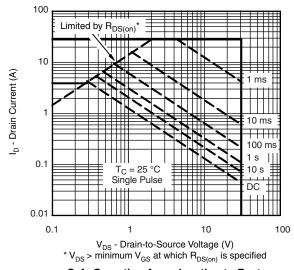
Source-Drain Diode Forward Voltage







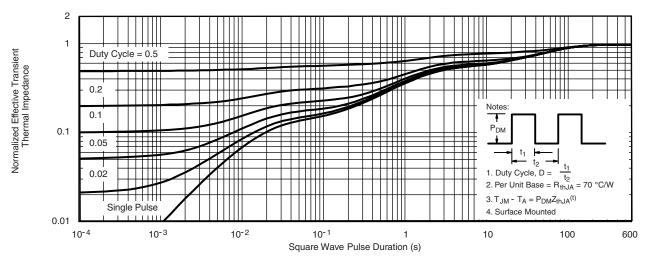
Single Pulse Power, Junction-to-Ambient



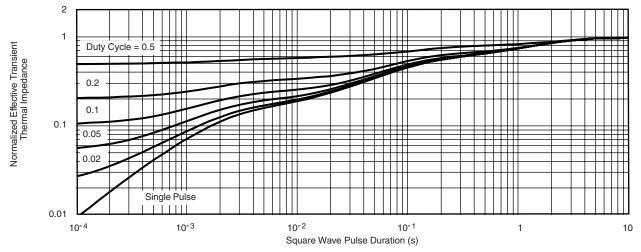
Safe Operating Area, Junction-to-Foot



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72245.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B